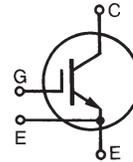


High Voltage IGBT

IXGN200N170



$$V_{CES} = 1700V$$

$$I_{C90} = 160A$$

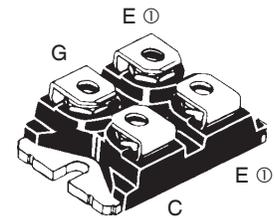
$$V_{CE(sat)} \leq 2.6V$$

$$t_{fi(typ)} = 535ns$$

SOT-227B, miniBLOC

E153432

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1700	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1700	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	280	A
I_{LRMS}	Terminal Current Limit	200	A
I_{C90}	$T_C = 90^\circ C$	160	A
I_{CM}	$T_C = 25^\circ C$, 1ms	1050	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 1\Omega$ Clamped Inductive Load	$I_{CM} = 300$	A
		1360	V
P_C	$T_C = 25^\circ C$	1250	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
V_{ISOL}	50/60Hz $t = 1min$ $I_{ISOL} \leq 1mA$ $t = 1s$	2500	V~
		3000	V~
M_d	Mounting Torque	1.5/13	Nm/lb.in
	Terminal Connection Torque	1.3/11.5	Nm/lb.in
Weight		30	g



G = Gate, C = Collector, E = Emitter
 ① either emitter terminal can be used as Main or Kelvin Emitter

Features

- miniBLOC, with Aluminium Nitride Isolation
- International Standard Package
- Isolation Voltage 2500V~
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

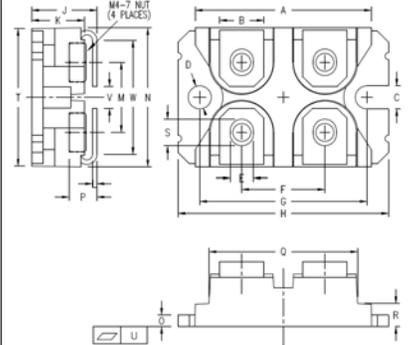
Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Welding Machines

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 3mA$, $V_{GE} = 0V$	1700		V
$V_{GE(th)}$	$I_C = 1mA$, $V_{CE} = V_{GE}$	3.5		V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 125^\circ C$			25 μA
				5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 200 nA
$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, Note 1 $T_J = 125^\circ C$	2.1		V
		2.5		V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	50	82	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		12.5	nF
C_{oes}			580	pF
C_{res}			220	pF
$Q_{g(on)}$	$I_C = 200\text{A}_0, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		540	nC
Q_{ge}			78	nC
Q_{gc}			265	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		37	ns
t_{ri}			133	ns
E_{on}			28	mJ
$t_{d(off)}$			320	ns
t_{fi}			535	ns
E_{off}		30	mJ	
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 100\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 1\Omega$ Note 2		40	ns
t_{ri}			143	ns
E_{on}			31	mJ
$t_{d(off)}$			430	ns
t_{fi}			610	ns
E_{off}		44	mJ	
R_{thJC}				0.10 $^\circ\text{C/W}$
R_{thCS}		0.05		$^\circ\text{C/W}$

SOT-227B miniBLOC (IXGN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.489	1.505	37.80	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1
V	.130	.180	3.30	4.57
W	.780	.830	19.81	21.08

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

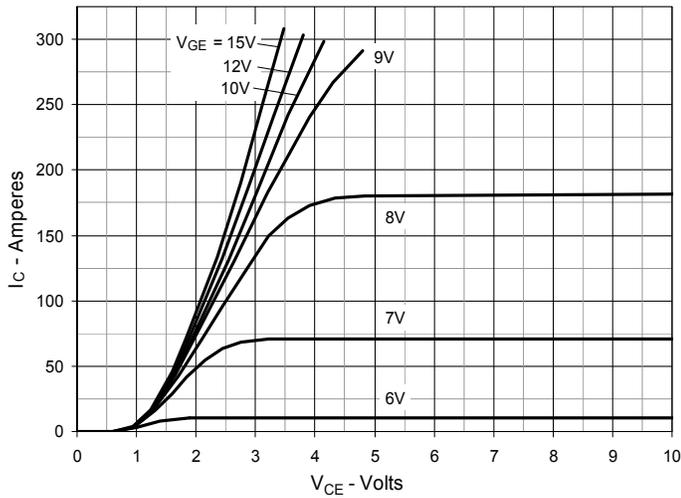


Fig. 2. Output Characteristics @ $T_J = 125^\circ\text{C}$

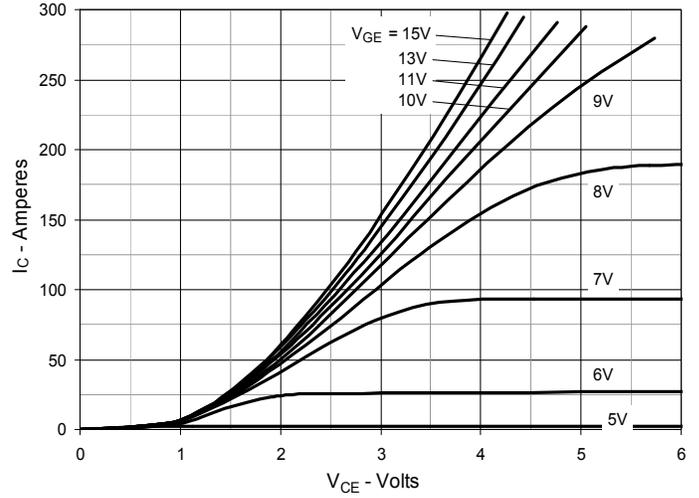


Fig. 3. Dependence of $V_{CE(sat)}$ on Junction Temperature

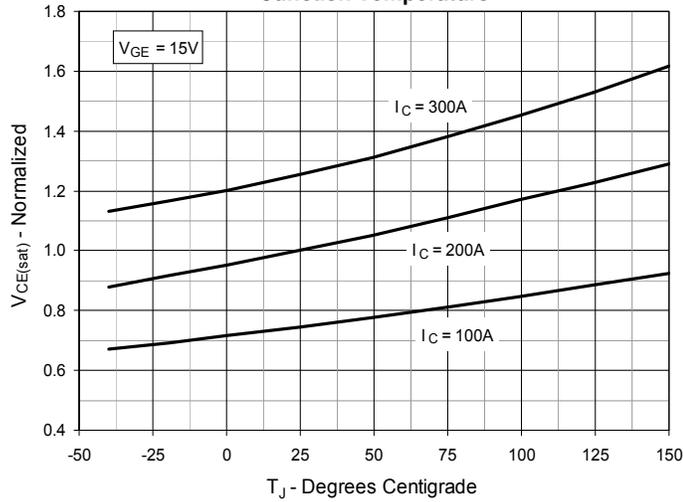


Fig. 4. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

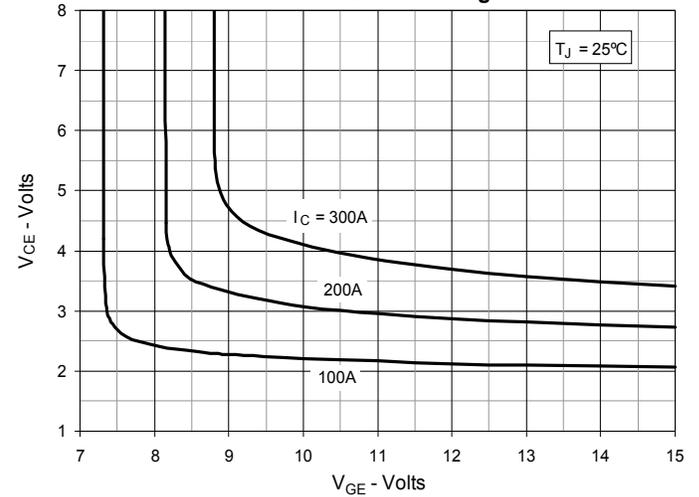


Fig. 5. Input Admittance

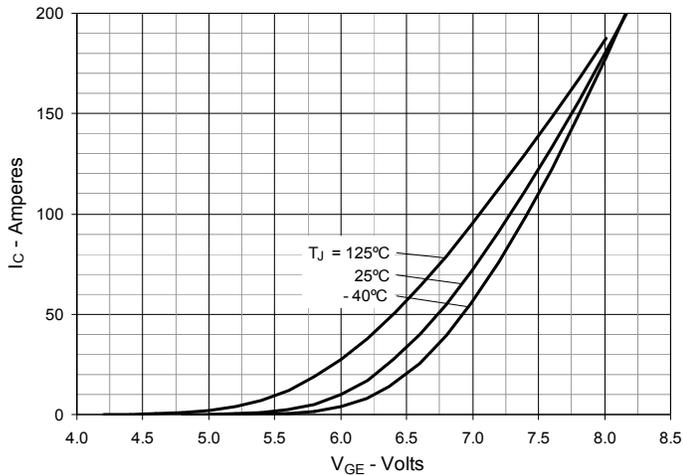


Fig. 6. Transconductance

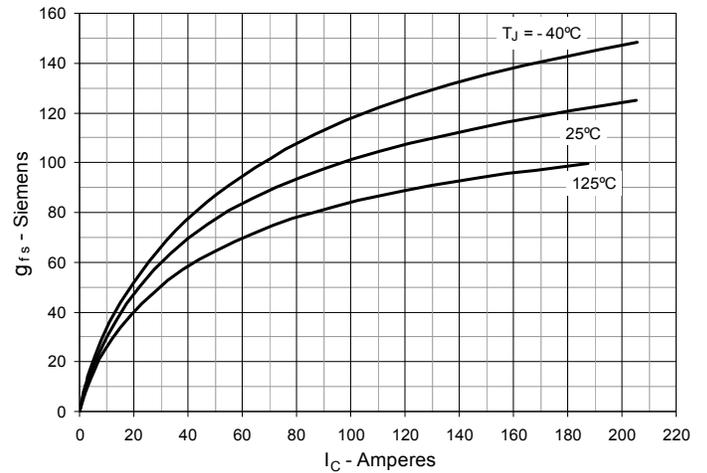


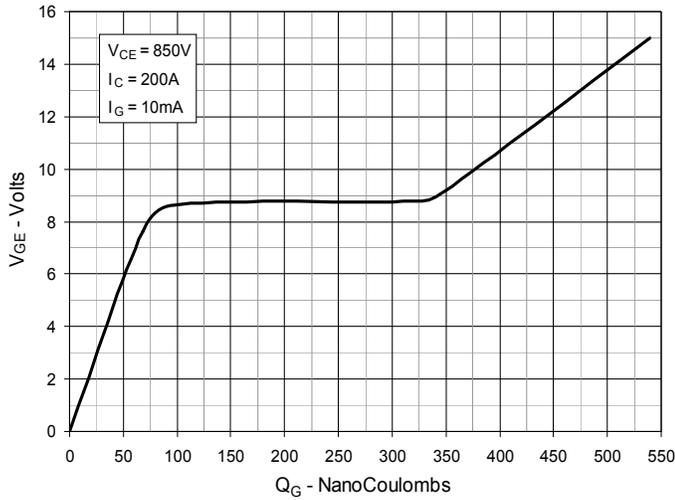
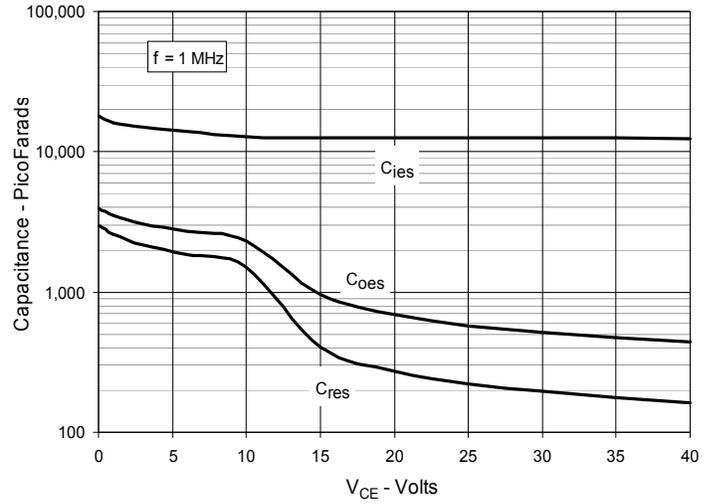
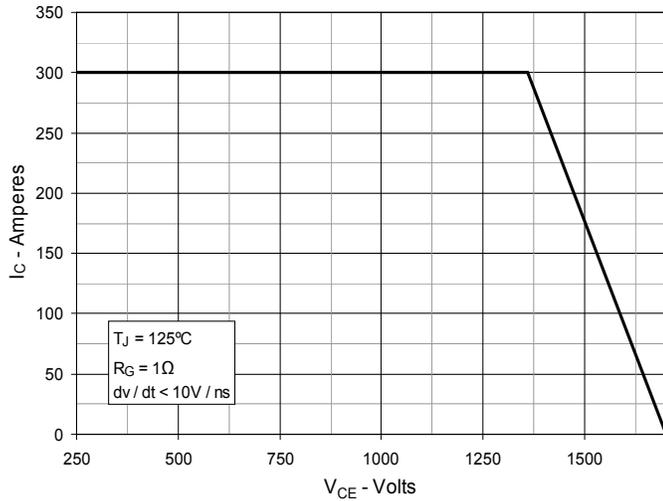
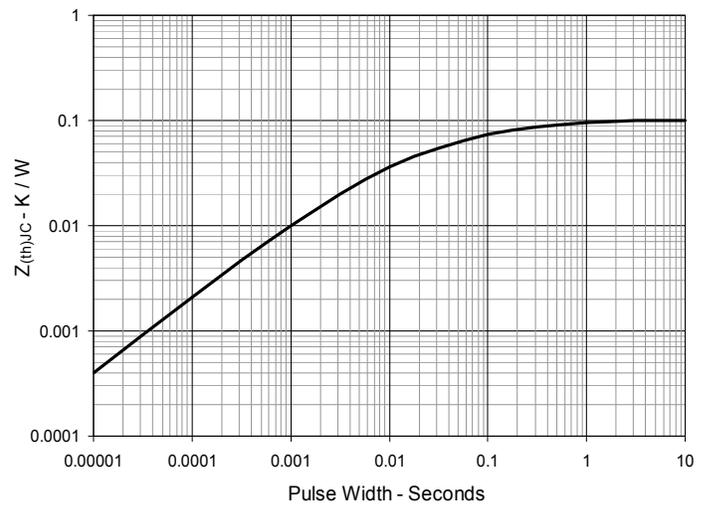
Fig. 7. Gate Charge

Fig. 8. Capacitance

Fig. 9. Reverse-Bias Safe Operating Area

Fig. 10. Maximum Transient Thermal Impedance


Fig. 11. Inductive Switching Energy Loss vs. Gate Resistance

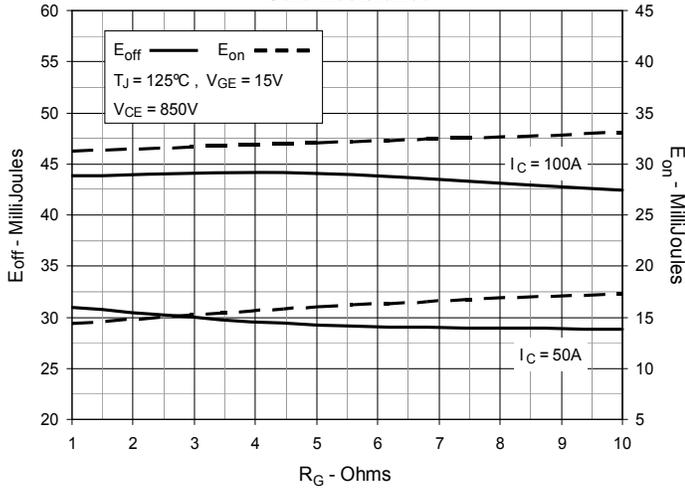


Fig. 12. Inductive Switching Energy Loss vs. Collector Current

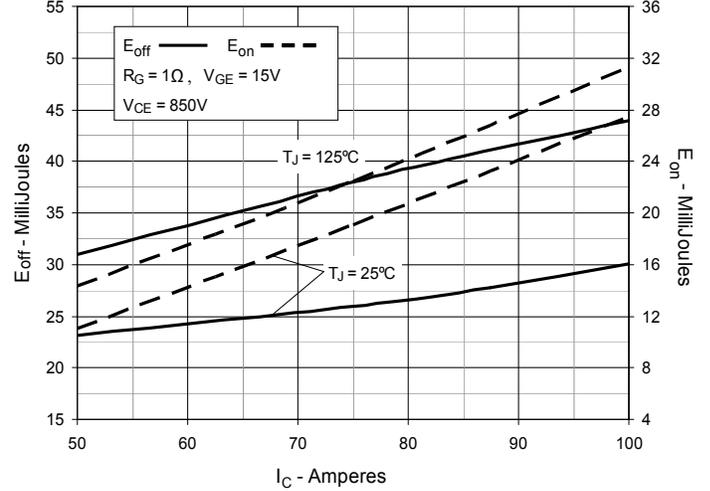


Fig. 13. Inductive Switching Energy Loss vs. Junction Temperature

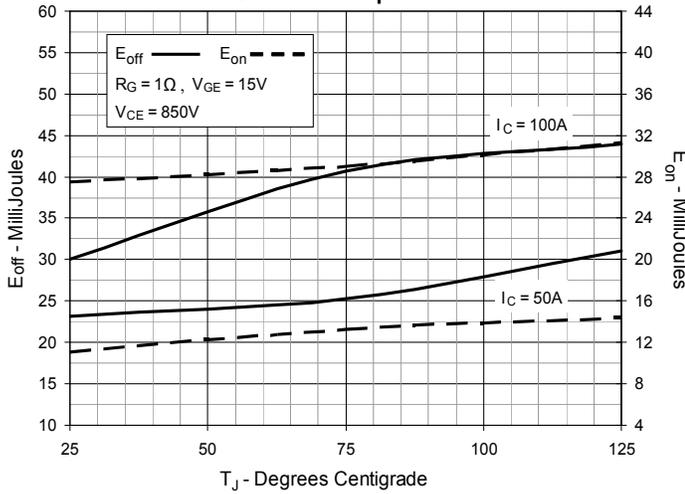


Fig. 14. Inductive Turn-off Switching Times vs. Gate Resistance

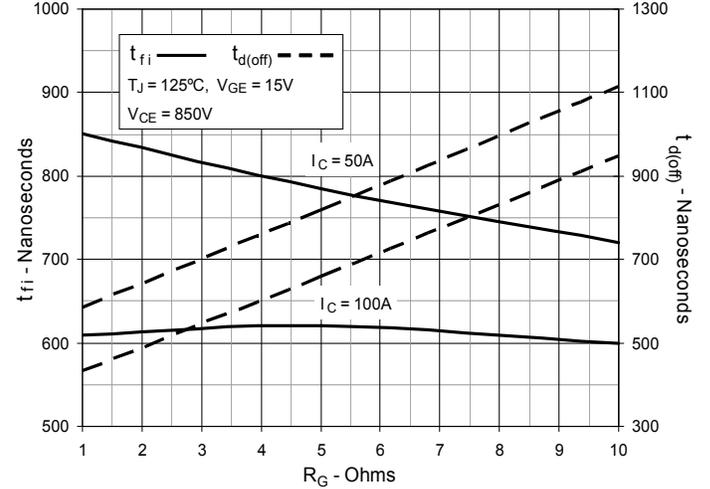


Fig. 15. Inductive Turn-off Switching Times vs. Collector Current

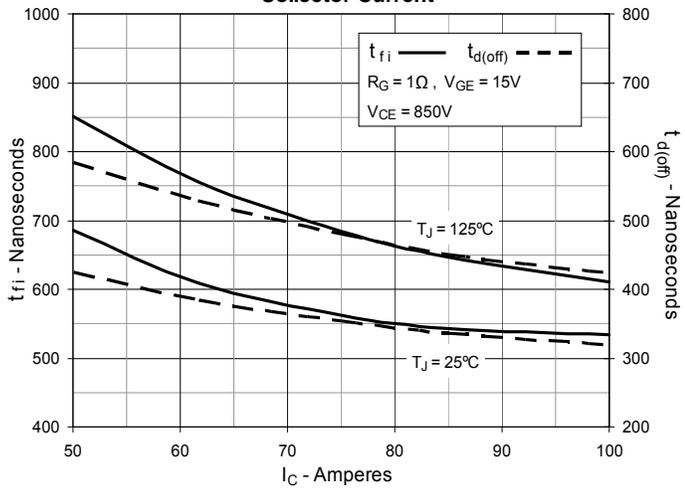


Fig. 16. Inductive Turn-off Switching Times vs. Junction Temperature

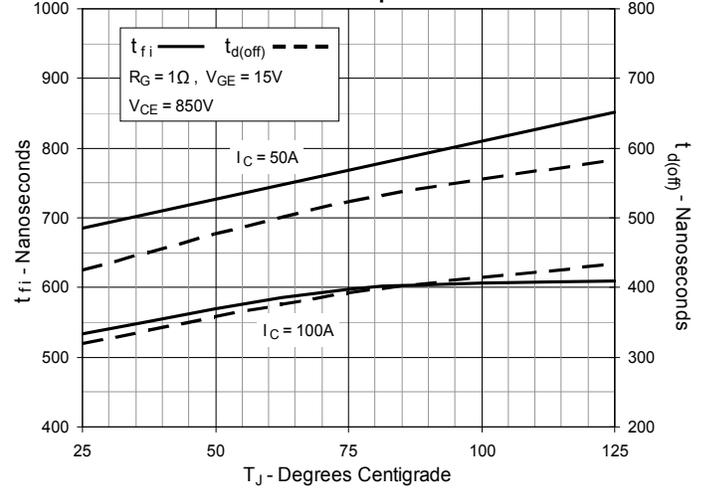
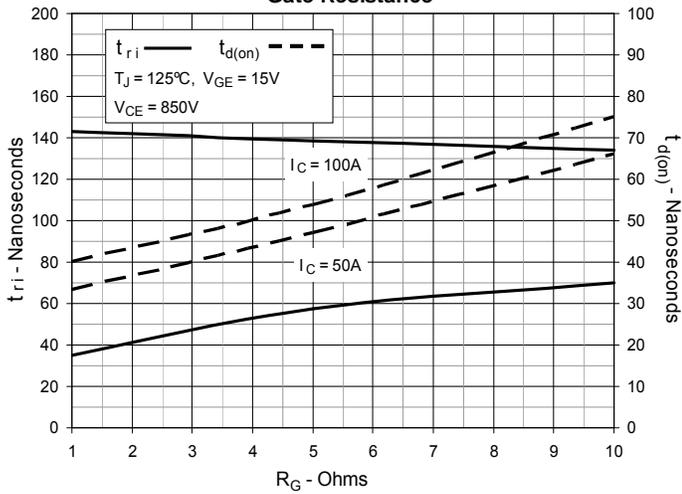
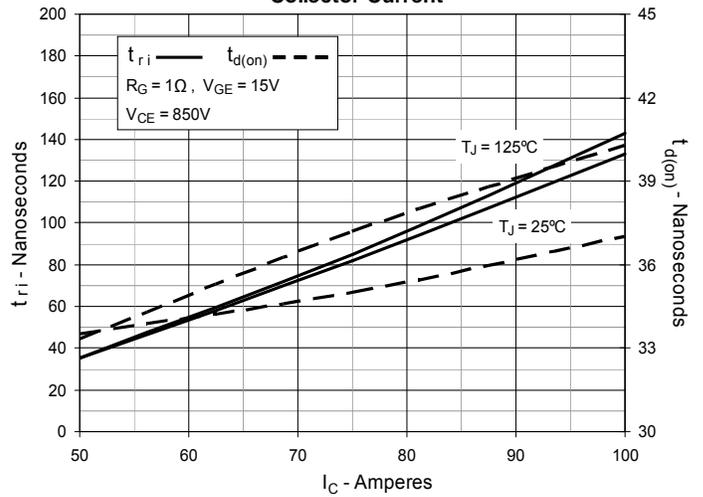


Fig. 17. Inductive Turn-on Switching Times vs. Gate Resistance

Fig. 18. Inductive Turn-on Switching Times vs. Collector Current

Fig. 19. Inductive Turn-on Switching Times vs. Junction Temperature
